



General Description

SFGMOS[®] MOSFET is based on Oriental Semiconductor's unique device design to achieve low $R_{DS(ON)}$, low gate charge, fast switching and excellent avalanche characteristics. The high V_{th} series is specially optimized for high systems with gate driving voltage greater than 10V.

Features

- Low $R_{DS(ON)}$ & FOM
- Extremely low switching loss
- Excellent stability and uniformity
- Fast switching and soft recovery



Applications

- Switching mode power supply
- Motor driver
- Battery protection
- DC-DC convertor
- Solar inverter
- UPS and energy inverter

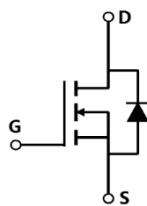
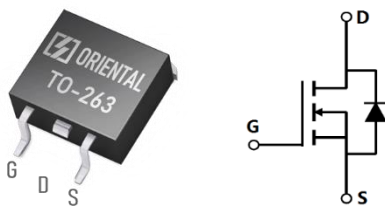
Key Performance Parameters

Parameter	Value	Unit
V_{DS}	120	V
I_D , pulse	330	A
$R_{DS(ON)}$, max @ $V_{GS}=10V$	6.5	m Ω
Q_g	68.9	nC
PD	192	W

Marking Information

Product Name	Package	Marking
SFG110N12KF	TO263	SFG110N12K

Package & Pin information



Absolute Maximum Ratings at $T_j=25^{\circ}\text{C}$ unless otherwise noted

Parameter	Symbol	Value	Unit
Drain source voltage	V_{DS}	120	V
Gate source voltage	V_{GS}	± 20	V
Continuous drain current ¹⁾ , $T_C=25^{\circ}\text{C}$	I_D	110	A
Continuous drain current ¹⁾ , $T_C=100^{\circ}\text{C}$		69.5	A
Pulsed drain current ²⁾ , $T_C=25^{\circ}\text{C}$	$I_{D, \text{pulse}}$	330	A
Continuous diode forward current ¹⁾ , $T_C=25^{\circ}\text{C}$	I_S	110	A
Diode pulsed current ²⁾ , $T_C=25^{\circ}\text{C}$	$I_{S, \text{pulse}}$	330	A
Power dissipation ³⁾ , $T_C=25^{\circ}\text{C}$	P_D	192	W
Single pulsed avalanche energy ⁵⁾	E_{AS}	400	mJ
Operation and storage temperature	T_{stg}, T_j	-55 to 150	$^{\circ}\text{C}$

Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal resistance, junction-case	$R_{\theta JC}$	0.65	$^{\circ}\text{C/W}$
Thermal resistance, junction-ambient ⁴⁾	$R_{\theta JA}$	62	$^{\circ}\text{C/W}$

Electrical Characteristics at $T_j=25^{\circ}\text{C}$ unless otherwise specified

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Drain-source breakdown voltage	BV_{DSS}	120			V	$V_{GS}=0\text{ V}, I_D=250\text{ }\mu\text{A}$
Gate threshold voltage	$V_{GS(th)}$	2.0		4.0	V	$V_{DS}=V_{GS}, I_D=250\text{ }\mu\text{A}$
Drain-source on-state resistance	$R_{DS(ON)}$		5.0	6.5	$\text{m}\Omega$	$V_{GS}=10\text{ V}, I_D=30\text{ A}$
Gate-source leakage current	I_{GSS}			100	nA	$V_{GS}=20\text{ V}$
Drain-source leakage current	I_{DSS}			1	μA	$V_{DS}=120\text{ V}, V_{GS}=0\text{ V}$

Dynamic Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Input capacitance	C_{iss}		5823		pF	$V_{GS}=0\text{ V}$, $V_{DS}=50\text{ V}$, $f=100\text{ kHz}$
Output capacitance	C_{oss}		779		pF	
Reverse transfer capacitance	C_{rss}		17.5		pF	
Turn-on delay time	$t_{d(on)}$		30.3		ns	$V_{GS}=10\text{ V}$, $V_{DS}=50\text{ V}$, $R_G=2\ \Omega$, $I_D=25\text{ A}$
Rise time	t_r		33		ns	
Turn-off delay time	$t_{d(off)}$		59.5		ns	
Fall time	t_f		11.7		ns	

Gate Charge Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Total gate charge	Q_g		68.9		nC	$V_{GS}=10\text{ V}$, $V_{DS}=50\text{ V}$, $I_D=25\text{ A}$
Gate-source charge	Q_{gs}		18.1		nC	
Gate-drain charge	Q_{gd}		15.9		nC	
Gate plateau voltage	$V_{plateau}$		4.8		V	

Body Diode Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Diode forward voltage	V_{SD}			1.3	V	$I_S=30\text{ A}$, $V_{GS}=0\text{ V}$
Reverse recovery time	t_{rr}		85		ns	$V_R=50\text{ V}$, $I_S=25\text{ A}$, $di/dt=100\text{ A}/\mu\text{s}$
Reverse recovery charge	Q_{rr}		240		nC	
Peak reverse recovery current	I_{rrm}		4.6		A	

Note

- 1) Calculated continuous current based on maximum allowable junction temperature.
- 2) Repetitive rating; pulse width limited by max. junction temperature.
- 3) P_d is based on max. junction temperature, using junction-case thermal resistance.
- 4) The value of $R_{\theta JA}$ is measured with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with $T_a=25\text{ }^{\circ}\text{C}$.
- 5) $V_{DD}=50\text{ V}$, $V_{GS}=10\text{ V}$, $L=0.3\text{ mH}$, starting $T_j=25\text{ }^{\circ}\text{C}$.

Electrical Characteristics Diagrams

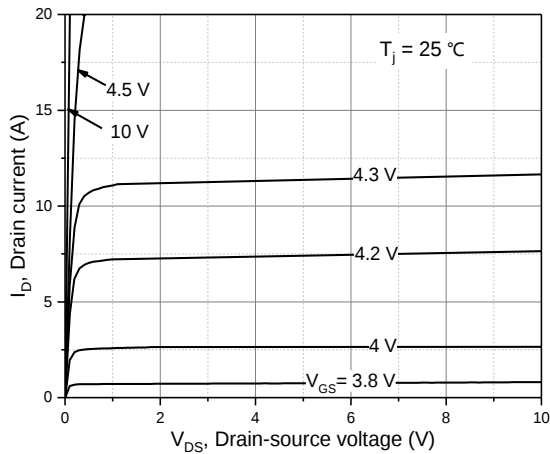


Figure 1. Typ. output characteristics

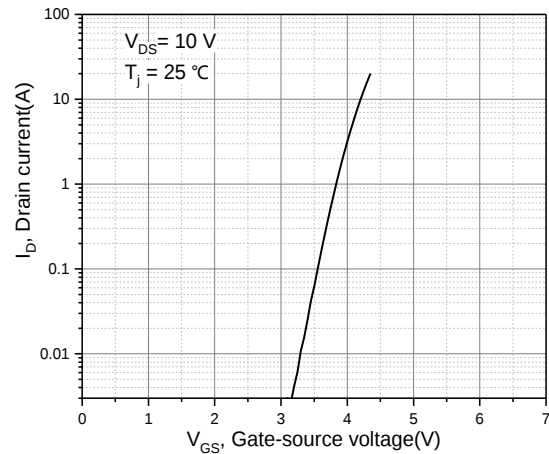


Figure 2. Typ. transfer characteristics

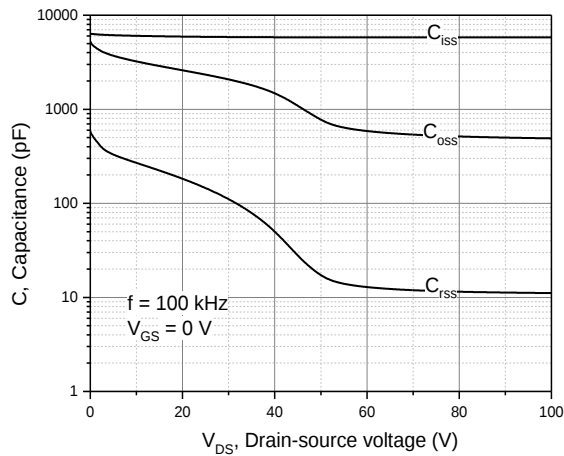


Figure 3. Typ. capacitances

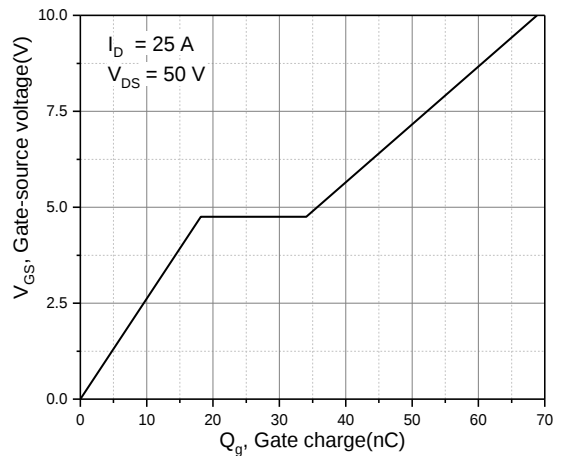


Figure 4. Typ. gate charge

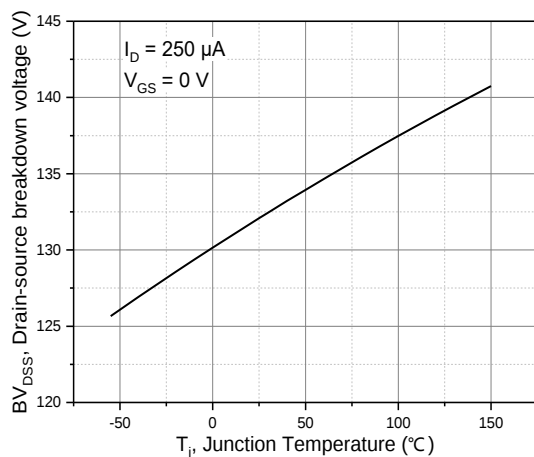


Figure 5. Drain-source breakdown voltage

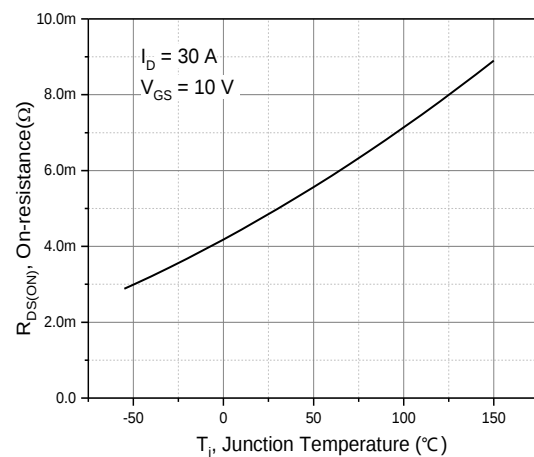


Figure 6. Drain-source on-state resistance

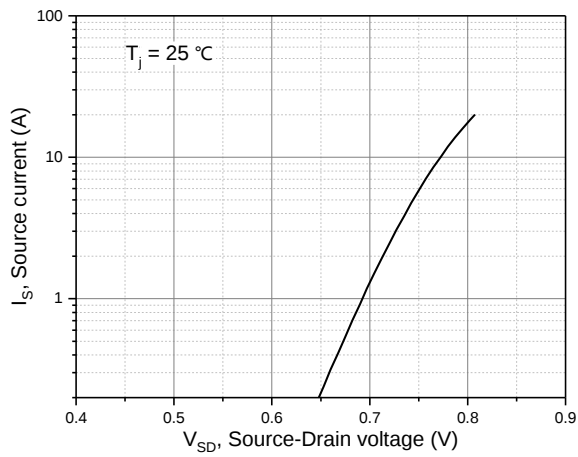


Figure 7. Forward characteristic of body diode

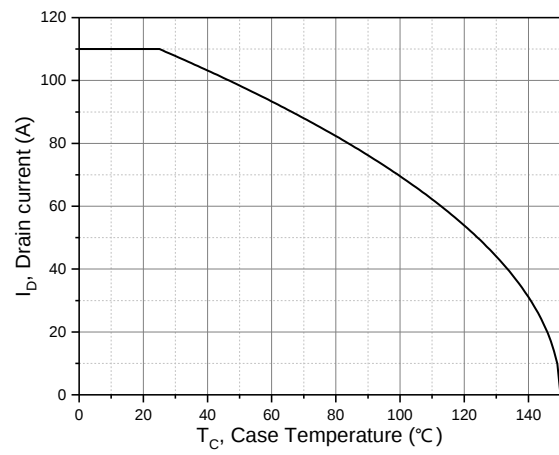


Figure 8. Drain current

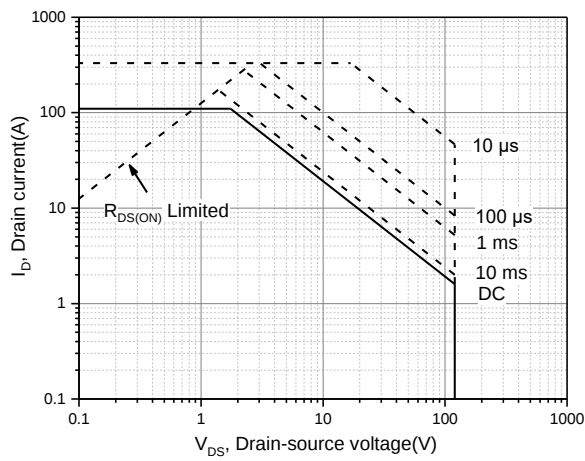


Figure 9. Safe operation area $T_C=25\text{ }^{\circ}\text{C}$

Test circuits and waveforms



Figure 1. Gate charge test circuit & waveform



Figure 2. Switching time test circuit & waveforms

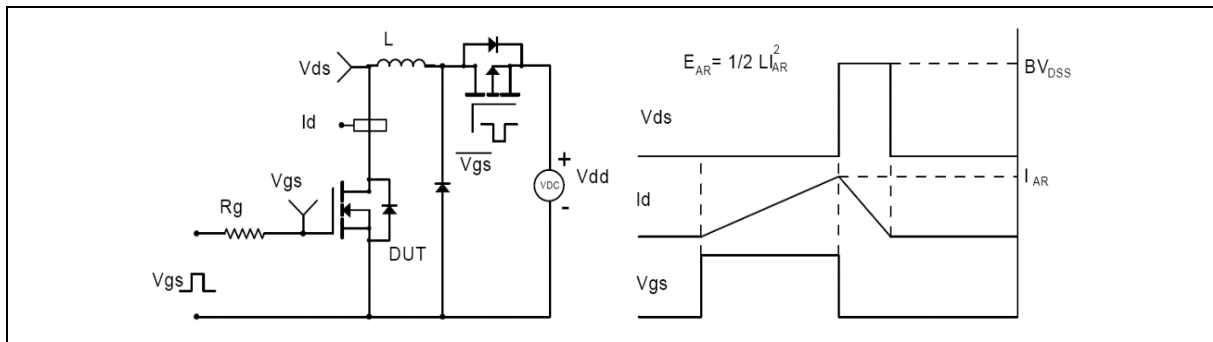
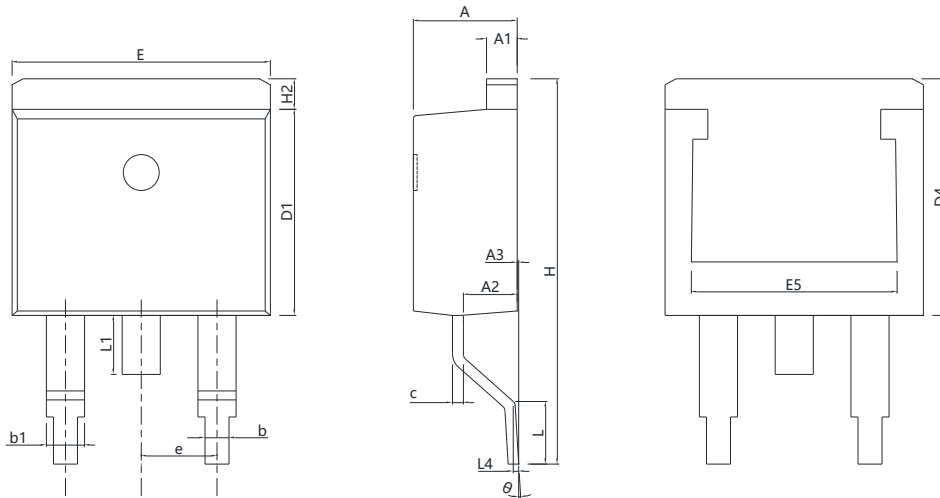


Figure 3. Unclamped inductive switching (UIS) test circuit & waveforms



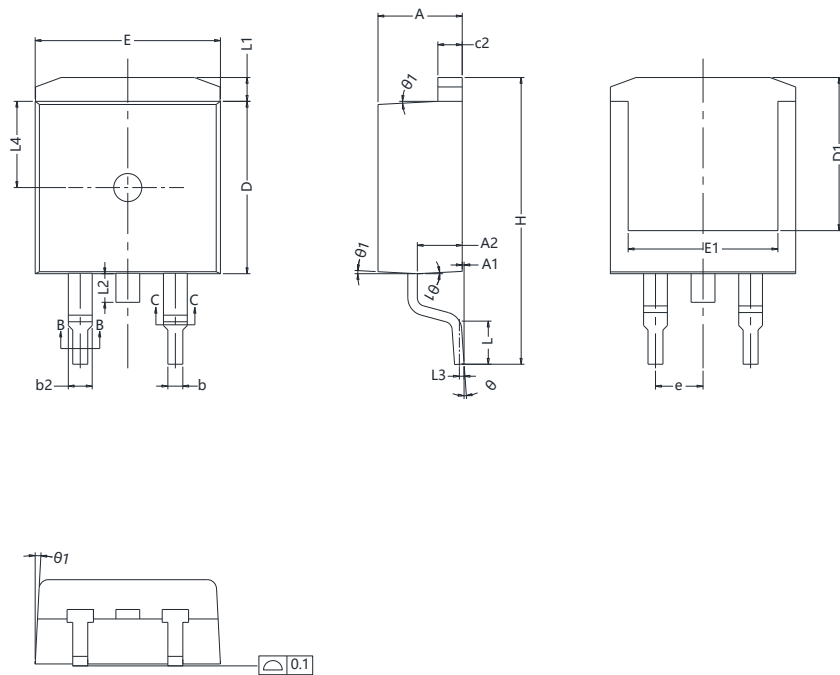
Figure 4. Diode reverse recovery test circuit & waveforms

Package Information



Symbol	mm		
	Min	Nom	Max
A	4.37	4.57	4.77
A1	1.22	1.27	1.42
A2	2.49	2.69	2.89
A3	0.00	0.13	0.25
b	0.70	0.81	0.96
b1	1.17	1.27	1.47
c	0.30	0.38	0.53
D1	8.50	8.70	8.90
D4	6.60	-	-
E	9.86	10.16	10.36
E5	7.06	-	-
e	2.54 BSC		
H	14.70	15.10	15.50
H2	1.07	1.27	1.47
L	2.00	2.30	2.60
L1	1.40	1.55	1.70
L4	0.25 BSC		
θ	0°	5°	9°

Version 1: TO263-P package outline dimension

Package Information


Symbol	mm		
	Min	Nom	Max
A	4.40	4.50	4.60
A1	0.00	0.10	0.25
A2	2.20	2.40	2.60
b	0.76	-	0.89
b2	1.23	-	1.37
c2	1.25	1.30	1.35
D	9.10	9.20	9.30
D1	8.00	-	-
E	9.80	9.90	10.00
E1	7.80	-	-
e	2.54 BSC		
H	14.90	15.30	15.70
L	2.00	2.30	2.60
L1	1.17	1.27	1.40
L2	-	-	1.75
L3	0.25 BSC		
L4	4.60 REF		
θ	0°	-	8°
θ1	1°	3°	5°

Version 2: TO263-J package outline dimension

Ordering Information

Package Type	Units/ Reel	Reels / Inner Box	Units/ Inner Box	Inner Boxes/ Carton Box	Units/ Carton Box
TO263-P	800	1	800	5	4000
TO263-J	800	1	800	10	8000

Product Information

Product	Package	Pb Free	RoHS	Halogen Free
SFG110N12KF	TO263	yes	yes	yes

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